

L Number	Hits	Search Text	DB	Time stamp
1	90355	(anneal\$3 heat\$3 bak\$3 thermal thermally) near15 (hydrogen "H.sub.2" HCl)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/21 17:56
8	9612	((anneal\$3 heat\$3 bak\$3 thermal thermally) near15 (hydrogen "H.sub.2" HCl)) near15 (silicon semiconductor substrate SOI wafer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/21 17:56
15	211	((anneal\$3 heat\$3 bak\$3 thermal thermally) near15 (hydrogen "H.sub.2" HCl)) near15 (silicon semiconductor substrate SOI wafer)) same (atm or (atmospheric adj pressure) or ("750" "760") adj torr))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/09/21 17:58